

#### **Description**

The RUE002N02 uses advanced trench technology to provide excellent R<sub>DS(ON)</sub>, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a

Battery protection or in other Switching application.

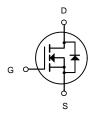


**SOT-523** 

#### **General Features**

 $V_{DS} = 20V I_{D} = 0.8A$ 

 $R_{DS(ON)}$  < 250 mQ@  $V_{GS}$ =4.5V  $R_{DS(ON)} < 360 \text{ m}\Omega @ V_{GS} = 2.5V$ 



N-Channel MOSFET

#### **Application**

Battery protection

Load switch

Uninterruptible power supply

**Package Marking and Ordering Information** 

Product ID	Pack	Brand	Qty(PCS)
RUE002N02	SOT-523	HXY MOSFET	3000

## Absolute Maximum Ratings (T<sub>A</sub>=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V <sub>D</sub> s	Drain-Source Voltage	20	V
Vgs	Gate-Source Voltage	±8	V
ID	Drain Current-Continuous	0.8	А
P <sub>D</sub>	Maximum Power Dissipation	0.15	W
Тл,Тятв	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	850	°C/W



## Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

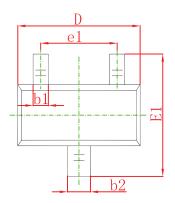
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
STATIC CHARACTERISTICE						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =250µA	20			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> =20V,V <sub>GS</sub> = 0V			1	μΑ
Gate-body leakage current	I <sub>GSS</sub>	V <sub>GS</sub> =±8V, V <sub>DS</sub> = 0V			±10	μA
Gate threshold voltage (note2)	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.5	0.7	1.0	V
Desir sames as a 11	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =0.5A		0.18	0.25	Ω
Drain-source on-resistance (note2)		V <sub>GS</sub> =2.5V, I <sub>D</sub> =0.5A		0.27	0.36	Ω
Maximum Continuous Drain to Source Diode Forward Current	Is				0.8	А
Maximum Pulsed Drain to Source Diode Forward Current	I <sub>SM</sub>				1.2	А
Diode forward voltage	V <sub>SD</sub>	I <sub>S</sub> =0.5A, V <sub>GS</sub> =0V			1.2	V
DYNAMIC CHARACTERISTICS (note4)						
Input capacitance	C <sub>iss</sub>			50		pF
Output capacitance	Coss	V <sub>DS</sub> =16V,V <sub>GS</sub> =0V, f =1MHz		7		pF
Reverse transfer capacitance	Crss	1 1141112		4.5		pF
SWITCHING CHARACTERISTICS (no	te4)					
Turn-on delay time (note3)	t <sub>d(on)</sub>			2		nS
Turn-on rise time (note3)	t <sub>r</sub>	\\ _45\\\ _40\\ B _400		32		nS
Turn-off delay time (note3)	t <sub>d(off)</sub>	$V_{GS}$ =4.5V, $V_{DS}$ =10V, $R_L$ =10 $\Omega$		47		nS
Turn-off fall time (note3)	t <sub>f</sub>			22		nS

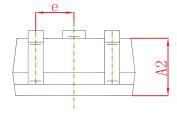
#### Notes:

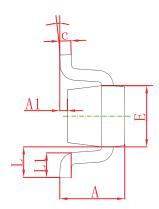
- 1. Surface mounted on FR4 board using the minimum recommended pad size.
- 2. Pulse Test : Pulse Width=300µs, Duty Cycle=2%.
- 3. Switching characteristics are independent of operating junction temperatures.
- 4. Guaranteed by design, not subject to producting.



## **SOT-523 Package Information**

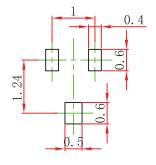






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	0.700	0.900	0.028	0.035	
A1	0.000	0.100	0.000	0.004	
A2	0.700	0.800	0.028	0.031	
b1	0.150	0.250	0.006	0.010	
b2	0.250	0.350	0.010	0.014	
С	0.100	0.200	0.004	0.008	
D	1.500	1.700	0.059	0.067	
E	0.700	0.900	0.028	0.035	
E1	1.450	1.750	0.057	0.069	
е	0.500 TYP.		0.020 TYP.		
e1	0.900	1.100	0.035	0.043	
L	0.400 REF.		0.016 REF.		
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

## **SOT-523 Suggested Pad Layout**



#### Note:

- 1. Controlling dimension: in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

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